

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK165V65Z5

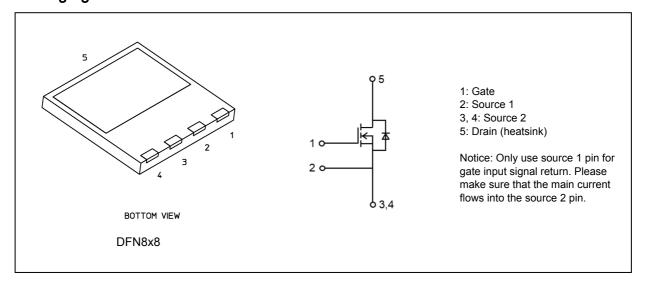
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 100 \text{ ns (typ.)}$
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.127 \Omega$ (typ.)
- (3) High-speed switching properties with lower capacitance.
- (4) Enhancement mode: V_{th} = 3.5 to 4.5 V (V_{DS} = 10 V, I_{D} = 0.73 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	650	V
Gate-source voltage	,	V_{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	18	Α
Drain current (pulsed)	(Note 1)	I _{DP}	72	
Power dissipation $(T_c = 25 ^{\circ}C)$,	P _D	150	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	282	mJ
Single-pulse avalanche current	,	I _{AS}	3.6	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	18	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	72	1
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.833	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 38.5 mH, I_{AS} = 3.6 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_		100	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	_	V
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 0.73 mA	3.5	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 9 A	_	0.127	0.165	Ω



6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	1660	_	pF
Reverse transfer capacitance		C _{rss}		_	1.6	_	
Output capacitance		C_{oss}		_	45	_	
Effective output capacitance (energy related)	(Note 3)	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	70	_	
Effective output capacitance (time related)	(Note 4)	C _{o(tr)}		_	435	_	
Gate resistance		r _g	V _{DS} = OPEN , f = 1 MHz	_	2.8	_	Ω
Switching time (rise time)		t _r	See Fig. 6.2.1	_	12	_	ns
Switching time (turn-on time)		t _{on}		_	38	_	
Switching time (fall time)		t _f		_	3.8	_	
Switching time (turn-off time)		t _{off}		_	65	_	
MOSFET dv/dt ruggedness		dv/dt	$V_{DS} \le V_{DSS}, I_D \le 9 A$	90	_	_	V/ns

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 V to 400 V. Note 4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 V to 400 V.

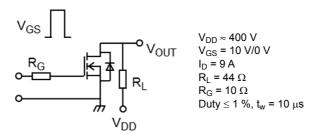


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$	_	30	_	nC
Gate-source charge 1	Q _{gs1}		_	10	_	
Gate-drain charge	Q _{qd}		_	10	_	

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 18 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time (Note	5) t _{rr}	V _{DD} = 400 V,	_	100	160	ns
Reverse recovery charge	Q _{rr}	$I_{DR} = 9 \text{ A}, V_{GS} = 0 \text{ V}$ - $dI_{DR}/dt = 100 \text{ A/}\mu\text{s}$	_	0.45	_	μС
Peak reverse recovery current	Irr	-uiDR/ut = 100 A/μs	_	9	_	Α
Diode dv/dt ruggedness	dv/dt	$V_{DD} \le 400 \text{ V}, I_{DR} \le 9 \text{ A}, V_{GS} = 0 \text{ V}$	70		_	V/ns

Note 5: Defined by design.



7. Marking (Note)

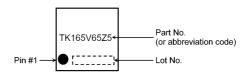


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

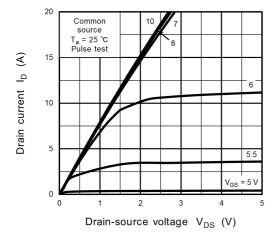
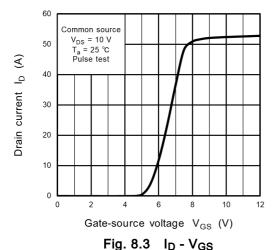
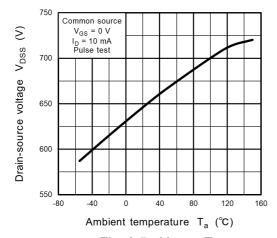
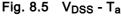


Fig. 8.1 I_D - V_{DS}







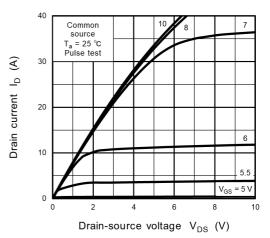


Fig. 8.2 I_D - V_{DS}

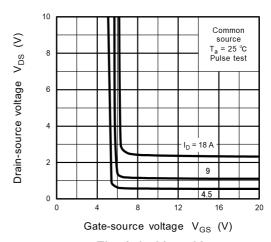


Fig. 8.4 VDS - VGS

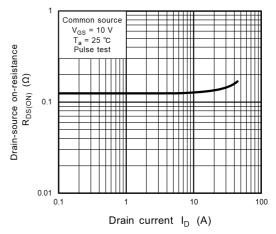
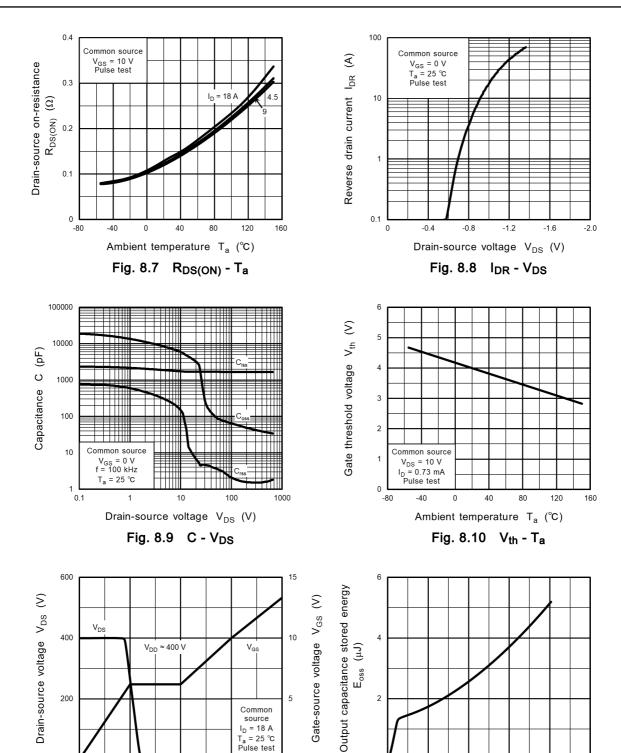


Fig. 8.6 R_{DS(ON)} - I_D





Total gate charge Q_g (nC) **Dynamic Input/Output Characteristics**

20

I_D = 18 A T_a = 25 °C Pulse test

40

0

Drain-source voltage V_{DS} (V) Fig. 8.12 Eoss - V_{DS}

0



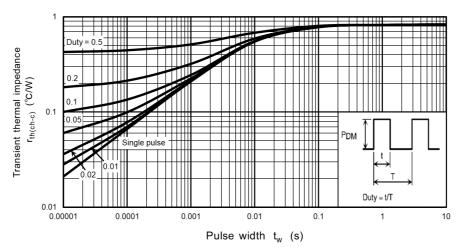


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

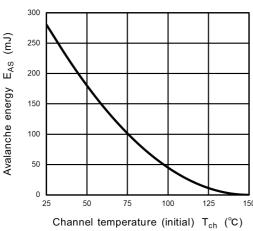
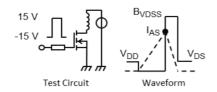


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)



$$V_{DD} = 90 \text{ V, L} = 38.5 \text{ mH} \quad E_{AS} = \frac{1}{2} \cdot \text{L} \cdot \text{I}_{AS}^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

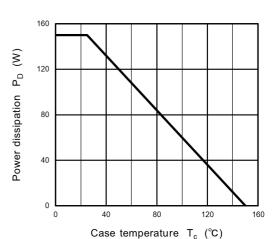


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

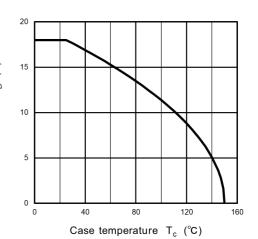


Fig. 8.17 $I_D - T_c$ (Guaranteed Maximum)

Fig. 8.16 Test Circuit/Waveform



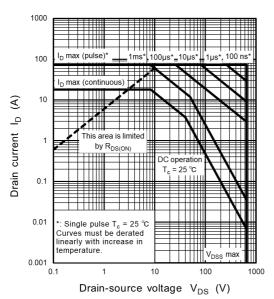


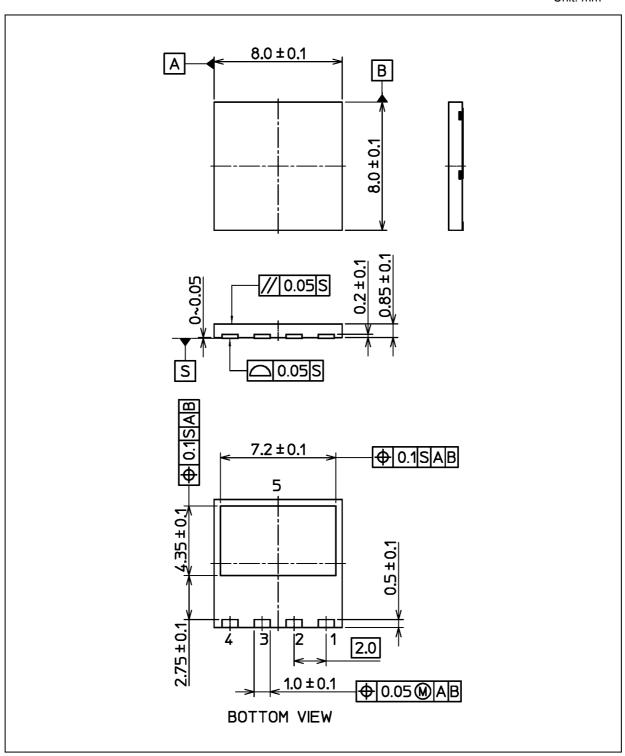
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	



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